

**P-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$ $T_A = +25^\circ C$
-50V	10Ω $V_{GS} = -5V$	-130mA

**Description**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

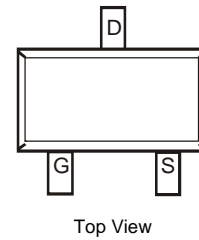
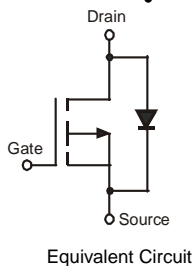
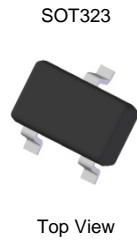
- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

**Features**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208 <sup>Ⓔ3</sup>
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Weight: 0.006 grams (approximate)

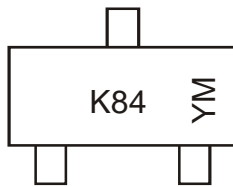
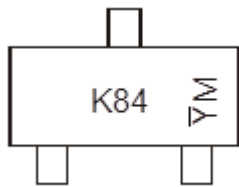


**Ordering Information** (Note 4 & 5)

Part Number	Compliance	Case	Packaging
BSS84W-7-F	Standard	SOT323	3000 / Tape & Reel
BSS84WQ-7-F	Automotive	SOT323	3000 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.
  5. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to [http://www.diodes.com/quality/product\\_grade\\_definitions/](http://www.diodes.com/quality/product_grade_definitions/).

**Marking Information**



K84 = Product Type Marking Code  
 YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)  
 YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)  
 Y or Y = Year (ex: A = 2013)  
 M = Month (ex: 9 = September)

Date Code Key

Year	2012	2013	2014	2015	2016	2017	2018
Code	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	-50	V
Drain-Gate Voltage (Note 6)	V <sub>DGR</sub>	-50	V
Gate-Source Voltage	V <sub>GSS</sub>	±20	V
Drain Current (Note 6)	I <sub>D</sub>	-130	mA
Pulsed Drain Current (Note 6)	I <sub>DM</sub>	-1	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50	-75	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
		—	—	-2	μA	V <sub>DS</sub> = -50V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +125°C
		—	—	-100	nA	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, T <sub>J</sub> = +25°C
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±10	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.8	-1.6	-2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	6	10	Ω	V <sub>GS</sub> = -5V, I <sub>D</sub> = -0.1A
Forward Transconductance	g <sub>FS</sub>	0.05	—	—	S	V <sub>DS</sub> = -25V, I <sub>D</sub> = -0.1A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iSS</sub>	—	—	45	pF	V <sub>DS</sub> = -25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	—	25	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	—	12	pF	
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	—	10	—	ns	V <sub>DD</sub> = -30V, I <sub>D</sub> = -0.27A, R <sub>GEN</sub> = 50Ω, V <sub>GS</sub> = -10V
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	18	—	ns	

- Notes:
6. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
  7. Short duration pulse test used to minimize self-heating effect.

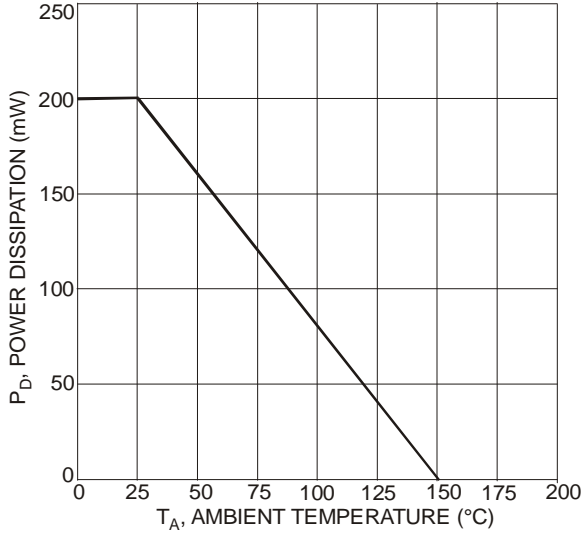


Fig. 1 Max Power Dissipation vs. Ambient Temperature

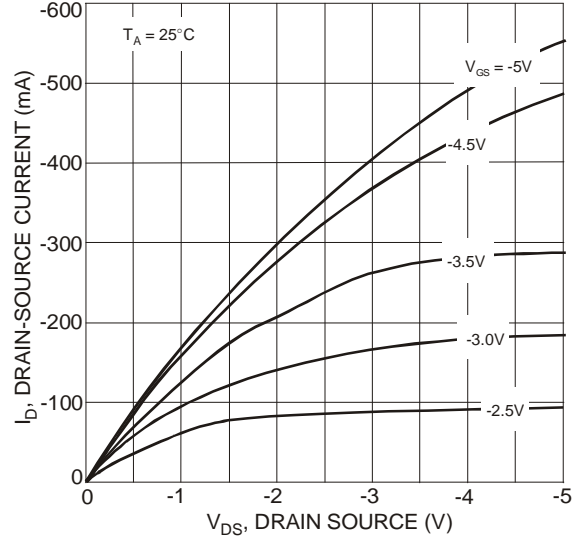


Fig. 2 Drain Source Current vs. Drain Source Voltage

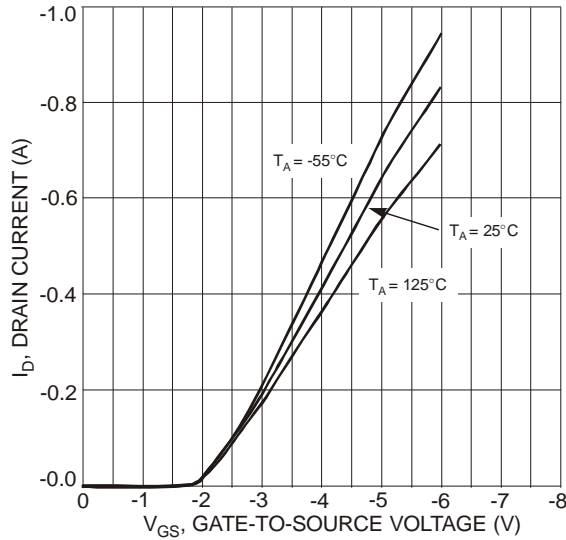


Fig. 3 Drain Current vs. Gate Source Voltage

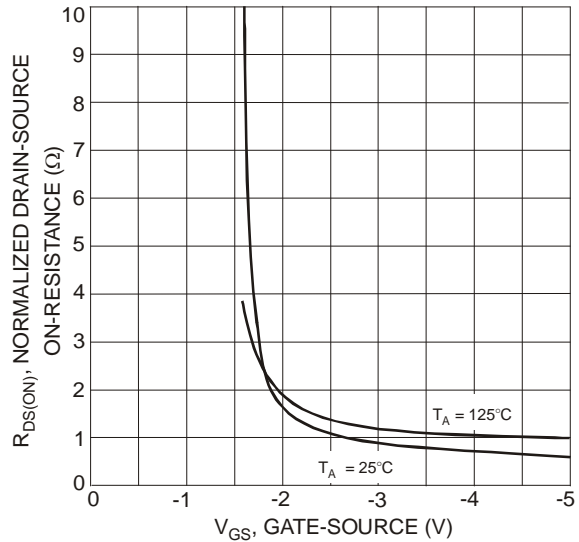


Fig. 4 On-Resistance vs. Gate-Source Voltage

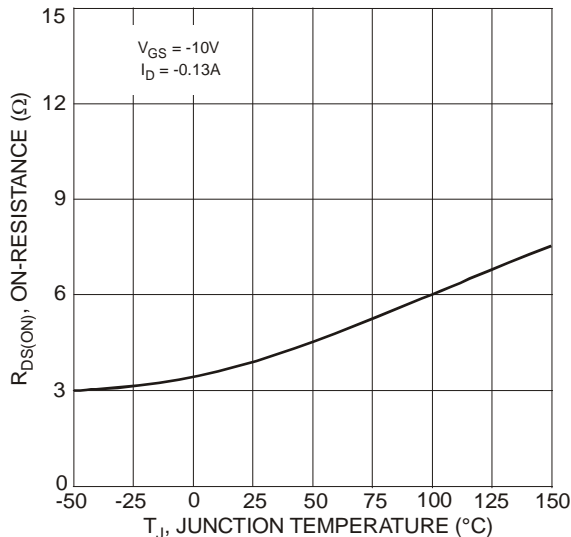


Fig. 5 On-Resistance vs. Junction Temperature

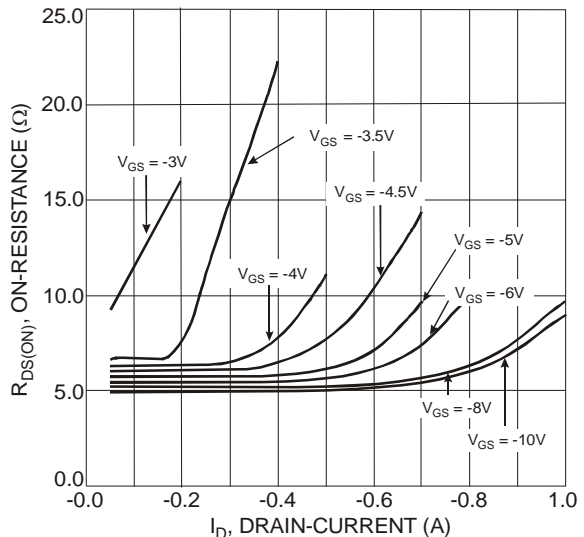
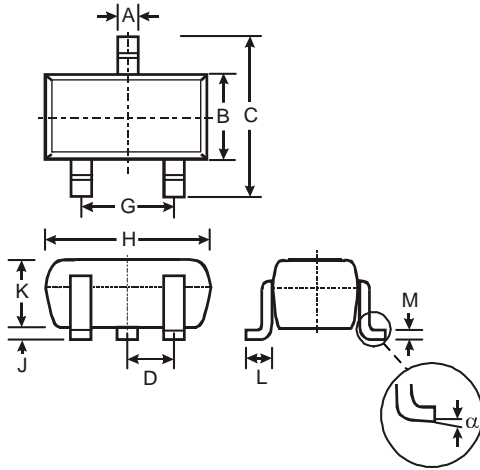


Fig. 6 On-Resistance vs. Drain-Current

**Package Outline Dimensions**

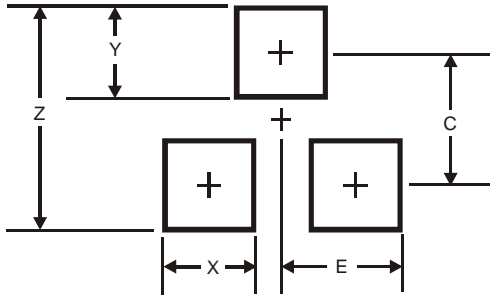
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	0.95
L	0.25	0.40	0.30
M	0.10	0.18	0.11
$\alpha$	0°	8°	-
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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Телефон: 8 (812) 309-75-97 (многоканальный)

Факс: 8 (812) 320-03-32

Электронная почта: [ocean@oceanchips.ru](mailto:ocean@oceanchips.ru)

Web: <http://oceanchips.ru/>

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, д. 2, корп. 4, лит. А